High Speed Low Power CAN, CAN FD Transceiver

Description

The NCV7344 CAN transceiver is the interface between a controller area network (CAN) protocol controller and the physical bus. The transceiver provides differential transmit capability to the bus and differential receive capability to the CAN controller.

The NCV7344 is an addition to the CAN high-speed transceiver family complementing NCV734x CAN stand-alone transceivers and previous generations such as AMIS42665, AMIS3066x, etc.

The NCV7344 guarantees additional timing parameters to ensure robust communication at data rates beyond 1 Mbps to cope with CAN flexible data rate requirements (CAN FD). These features make the NCV7344 an excellent choice for all types of HS-CAN networks, in nodes that require a low-power mode with wake-up capability via the CAN bus.

Features

- Compatible with ISO 11898-2:2016
- Specification for Loop Delay Symmetry up to 5 Mbps
- V_{IO} pin on NCV7344-3 Version Allowing Direct Interfacing with 3 V to 5 V Microcontrollers
- Very Low Current Standby Mode with Wake-up via the Bus
- Low Electromagnetic Emission (EME) and High Electromagnetic Immunity
- Very Low EME without Common-mode (CM) Choke
- No Disturbance of the Bus Lines with an Un-powered Node
- Transmit Data (TxD) Dominant Timeout Function
- Under All Supply Conditions the Chip Behaves Predictably
- Very High ESD Robustness of Bus Pins, >8 kV System ESD Pulses
- Thermal Protection
- Bus Pins Short Circuit Proof to Supply Voltage and Ground
- Bus Pins Protected Against Transients in an Automotive Environment
- These are Pb-free Devices

Quality

- Wettable Flank Package for Enhanced Optical Inspection
- NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable

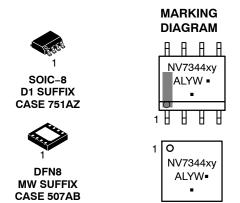
Typical Applications

- Automotive
- Industrial Networks



ON Semiconductor®

www.onsemi.com



NV7344xy= Specific Device Code

x = - or Ay = 0 or 3

– = long filter timeA = short filter time

A = Assembly Location

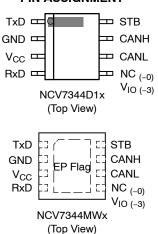
L = Wafer Lot Y = Year

W = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

PIN ASSIGNMENT



ORDERING INFORMATION

See detailed ordering and shipping information on page 11 of this data sheet.

BLOCK DIAGRAM

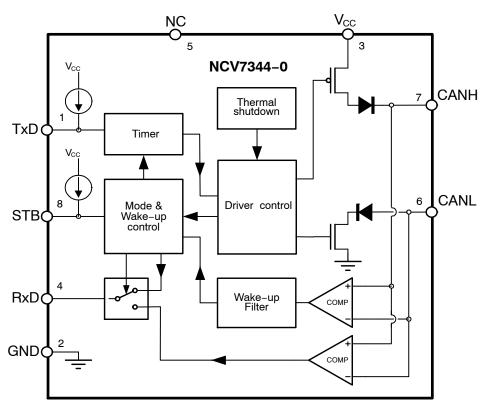


Figure 1. NCV7344-0 Block Diagram

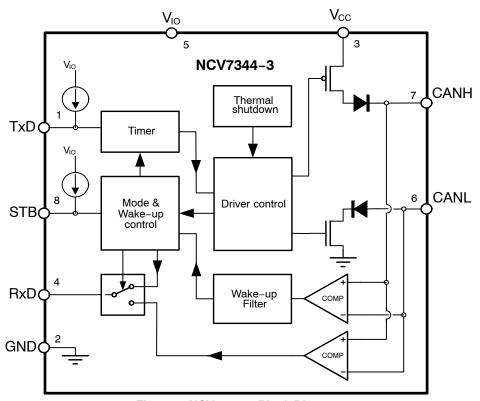


Figure 2. NCV7344-3 Block Diagram

TYPICAL APPLICATION

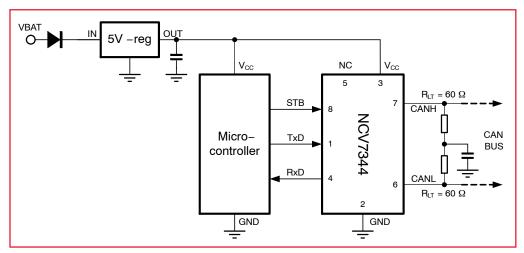


Figure 3. Application Diagram NCV7344-0

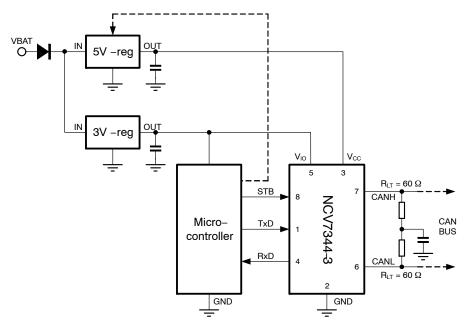


Figure 4. Application Diagram NCV7344-3

Table 1. PIN FUNCTION DESCRIPTION

Pin	n Name Description					
1	1 TxD Transmit data input; low input → dominant driver; internal pull-up current					
2	GND	Ground				
3	V _{CC}	Supply voltage				
4	RxD	Receive data output; dominant transmitter → low output				
5	NC	Not connected. On NCV7344–0 only				
5	V_{IO}	Digital Input / Output pins and other functions supply voltage. On NCV7344-3 only				
6	6 CANL Low-level CAN bus line (low in dominant mode)					
7	CANH	High-level CAN bus line (high in dominant mode)				
8	STB	STB Standby mode control input; internal pull-up current				
	EP	Exposed Pad. Recommended to connect to GND or left floating in application (DFN8 package only).				

FUNCTIONAL DESCRIPTION

Operating Modes

NCV7344 provides two modes of operation as illustrated in Table 2. These modes are selectable through pin STB.

Table 2. OPERATING MODES

Pin STB	Mode	Pin RxD				
Low	Normal	Low when bus dominant	High when bus recessive			
High	Standby	Follows the bus when wake-up detected	High when no wake-up request detected			

Normal Mode

In the normal mode, the transceiver is able to communicate via the bus lines. The signals are transmitted and received to the CAN controller via the pins TxD and RxD. The slopes on the bus lines outputs are optimized to give low EME.

Standby Mode

In standby mode both the transmitter and receiver are disabled and a very low-power differential receiver monitors the bus lines for CAN bus activity. The bus lines are biased to ground and supply current is reduced to a minimum, typically $10~\mu A$. When a wake-up request is detected by the low-power differential receiver, the signal is first filtered and then verified as a valid wake signal after a time period of t_{wake_filt} , the RxD pin is driven low by the transceiver (following the bus) to inform the controller of the wake-up request.

Wake-up

When a valid wake-up pattern (phase in order dominant – recessive – dominant) is detected during the standby mode the RxD pin follows the bus. Minimum length of each phase is $t_{wake\ filt}$ – see Figure 5.

Pattern must be received within t_{wake_to} to be recognized as valid wake-up otherwise internal logic is reset.

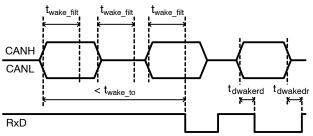


Figure 5. NCV7344 Wake-up Behavior

Overtemperature Detection

A thermal protection circuit protects the IC from damage by switching off the transmitter if the junction temperature exceeds a value of approximately 180°C. Because the transmitter dissipates most of the power, the power dissipation and temperature of the IC is reduced. All other IC functions continue to operate. The transmitter off–state resets when the temperature decreases below the shutdown threshold and pin TxD goes high. The thermal protection circuit is particularly needed when a bus line short circuits.

TxD Dominant Timeout Function

A TxD dominant timeout timer circuit prevents the bus lines being driven to a permanent dominant state (blocking all network communication) if pin TxD is forced permanently low by a hardware and/or software application failure. The timer is triggered by a negative edge on pin TxD. If the duration of the low–level on pin TxD exceeds the internal timer value $t_{\text{dom}(TxD)}$, the transmitter is disabled, driving the bus into a recessive state. The timer is reset by a positive edge on pin TxD.

This TxD dominant timeout time $t_{dom(TxD)}$ defines the minimum possible bit rate to 17 kbps.

Fail Safe Features

A current-limiting circuit protects the transmitter output stage from damage caused by accidental short circuit to either positive or negative supply voltage, although power dissipation increases during this fault condition.

Standby undervoltage on VCC pin prevents the chip sending data on the bus when there is not enough VCC supply voltage by entering standby mode. Undervoltage detection on VIO pin (NCV7344–3 version only) also causes transition to standby mode. Switch–off undervoltage detection level on supply pin(s) forces transceiver to disengage from the bus until the supply is recovered. After supply is recovered TxD pin must be first released to high to allow sending dominant bits again. Recovery time from undervoltage detection is equal to td(stb–nm) time.

The pins CANH and CANL are protected from automotive electrical transients (according to ISO 7637; see Figure 7). Pins TxD and STB are pulled high internally should the input become disconnected. Pins TxD, STB and RxD will be floating, preventing reverse supply should the VCC supply be removed.

VIO Supply Pin

The V_{IO} pin (available only on NCV7344–3 version) should be connected to microcontroller supply pin. By using V_{IO} supply pin shared with microcontroller the I/O levels between microcontroller and transceiver are properly adjusted. See Figure 4. Pin V_{IO} also provides the internal supply voltage for low–power differential receiver of the transceiver. This allows detection of wake–up request even when there is no supply voltage on pin V_{CC} .

ELECTRICAL CHARACTERISTICS

Definitions

All voltages are referenced to GND (pin 2). Positive currents flow into the IC. Sinking current means the current

is flowing into the pin; sourcing current means the current is flowing out of the pin.

ABSOLUTE MAXIMUM RATINGS

Table 3. ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Conditions	Min	Max	Unit
V _{SUP}	Supply voltage V _{CC} , V _{IO}		-0.3	+6	V
V _{CANH}	DC voltage at pin CANH	0 < V _{CC} < 5.25 V; no time limit	-42	+42	V
V _{CANL}	DC voltage at pin CANL	0 < V _{CC} < 5.25 V; no time limit	-42	+42	V
V _{CANH-CANL}	DC voltage between CANH and CANL		-42	+42	V
V _{I/O}	DC voltage at pin TxD, RxD, STB		-0.3	+6	V
V _{esdHBM}	Electrostatic discharge voltage at all pins, Component HBM	(Note 1)	-8	+8	kV
V _{esdCDM}	Electrostatic discharge voltage at all pins, Component CDM	(Note 2)	-750	+750	V
V _{esdIEC}	Electrostatic discharge voltage at pins CANH and CANL, System HBM (Note 4)	(Note 3)	-8	+8	kV
V _{schaff}	Voltage transients, pins CANH, CANL. According	test pulses 1	-100		V
	to ISO7637-3, Class C (Note 4)	test pulses 2a		+75	V
		test pulses 3a	-150		V
		test pulses 3b		+100	V
Latch-up	Static latch-up at all pins	(Note 5)		150	mA
T _{stg}	Storage temperature		-55	+150	°C
TJ	Maximum junction temperature		-40	+170	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 2. Standardized charged device model ESD pulses when tested according to AEC-Q100-011
- 3. System human body model electrostatic discharge (ESD) pulses in accordance to IEC 61000-4-2. Equivalent to discharging a 150 pF capacitor through a 330 Ω resistor referenced to GND.
- 4. Results were verified by external test house.
- 5. Static latch-up immunity: Static latch-up protection level when tested according to EIA/JESD78.

Table 4. THERMAL CHARACTERISTICS

Parameter	Symbol	Value	Unit
Thermal characteristics, SOIC-8 (Note 6) Thermal Resistance Junction-to-Air, Free air, 1S0P PCB (Note 7) Thermal Resistance Junction-to-Air, Free air, 2S2P PCB (Note 8)	$egin{array}{c} R_{ hetaJA} \ R_{ hetaJA} \end{array}$	131 81	°C/W °C/W
Thermal characteristics, DFN8 (Note 6) Thermal Resistance Junction-to-Air, Free air, 1S0P PCB (Note 7) Thermal Resistance Junction-to-Air, Free air, 2S2P PCB (Note 8)	$R_{ heta JA} \ R_{ heta JA}$	125 58	°C/W °C/W

Refer to ELECTRICAL CHARACTERISTICS, RECOMMENDED OPERATING RANGES and/or APPLICATION INFORMATION for Safe Operating parameters.

Standardized human body model electrostatic discharge (ESD) pulses in accordance to EIA-JESD22. Equivalent to discharging a 100 pF capacitor through a 1.5 kΩ resistor.

^{7.} Values based on test board according to EIA/JEDEC Standard JESD51-3, signal layer with 10% trace coverage.

^{8.} Values based on test board according to EIA/JEDEC Standard JESD51-7, signal layers with 10% trace coverage.

ELECTRICAL CHARACTERISTICS

Table 5. ELECTRICAL CHARACTERISTICS V_{CC} = 4.75 V to 5.25 V; V_{IO} = 2.8 to 5.25 V; T_{J} = -40 to +150°C; R_{LT} = 60 Ω , C_{LT} = 100 pF, C_{LT} not used, C_{RXD} = 15 pF unless specified otherwise.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
SUPPLY (Pin V	cc)					
V _{CC}	Power supply voltage	(Note 9)	4.75	5	5.25	V
I _{CC}	Supply current	Dominant; V _{TxD} = Low	20	45	70	mA
		Recessive; V _{TxD} = High	1.9	5	10	mA
I _{CCS}	Supply current in standby mode	T _J ≤ 100°C, (Note 10)	_	10	15	μΑ
V _{UVD(VCC)(stby)}	Standby undervoltage detection V _{CC} pin		3.5	4	4.3	V
V _{UVD(VCC)(swoff)}	Switch-off undervoltage detection V _{CC} pin		2.0	2.3	2.6	V
V _{IO} SUPPLY VO	DLTAGE (Pin V _{IO}) Only for NCV7344–3 version					-
V _{IO}	Supply voltage on pin V _{IO}		2.8	_	5.5	V
I _{IOS}	Supply current on pin V _{IO} in standby mode	T _J ≤ 100°C, (Note 10)	_	-	11	μΑ
I _{CCS}	Supply current on pin V _{CC} in standby mode	T _J ≤ 100°C, (Note 10)	-	0	4.0	μΑ
I _{IONM}	Supply current on pin V _{IO} during normal	Dominant; V _{TxD} = Low	0.45	0.65	0.9	mA
	mode	Recessive; V _{TxD} = High	0.32	0.43	0.58	1
V _{UVDVIO}	Undervoltage detection voltage on V _{IO} pin		2.0	2.3	2.6	V
TRANSMITTER	DATA INPUT (Pin TxD)		-	•	-	
V _{IH}	High-level input voltage	Output recessive	2.0	_	_	V
V _{IL}	Low-level input voltage	Output dominant	_	-	0.8	V
I _{IH}	High-level input current	$V_{TxD} = V_{CC}/V_{IO}$	-5	0	+5	μΑ
I _{IL}	Low-level input current	V _{TxD} = 0 V	-300	-150	-75	μΑ
C _i	Input capacitance	(Note 10)	_	5	10	pF
TRANSMITTER	MODE SELECT (Pin STB)					
V _{IH}	High-level input voltage	Standby mode	2.0	_	_	V
V _{IL}	Low-level input voltage	Normal mode	_	-	0.8	V
I _{IH}	High-level input current	$V_{STB} = V_{CC}/V_{IO}$	-1	0	+1	μΑ
I _{IL}	Low-level input current	V _{STB} = 0 V	-15	-	-1	μΑ
C _i	Input capacitance	(Note 10)	_	5	10	pF
RECEIVER DAT	TA OUTPUT (Pin RxD)					
Гон	High-level output current	Normal mode $V_{RxD} = V_{CC}/V_{IO} - 0.4 V$	-8	-3	-1	mA
I _{OL}	Low-level output current	V _{RxD} = 0.4 V	1	6	12	mA
BUS LINES (Pir	ns CANH and CANL)					
I _{o(rec)}	Recessive output current at pins CANH and CANL	-27 V < V _{CANH} , V _{CANL} < +32 V; Normal mode	-5	_	+5	mA
ILI	Input leakage current	0Ω < R(V _{CC} to GND) < 1 MΩ V _{CANL} = V _{CANH} = 5 V	-5	0	+5	μΑ
V _{o(rec)} (CANH)	Recessive output voltage at pin CANH	Normal mode, V_{TxD} = High; R_{LT} and C_{LT} not used	2.0	2.5	3.0	V
$V_{o(rec)(CANL)}$	Recessive output voltage at pin CANL	Normal mode, V_{TxD} = High; R_{LT} and C_{LT} not used	2.0	2.5	3.0	V
$V_{o(off)(CANH)}\\$	Recessive output voltage at pin CANH	Standby mode; R _{LT} and C _{LT} not used	-0.1	0	0.1	V

Table 5. ELECTRICAL CHARACTERISTICS V_{CC} = 4.75 V to 5.25 V; V_{IO} = 2.8 to 5.25 V; T_{J} = -40 to +150°C; R_{LT} = 60 Ω , C_{LT} = 100 pF, C_{LT} not used, C_{RXD} = 15 pF unless specified otherwise.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
BUS LINES (Pin	s CANH and CANL)					
$V_{o(off)(CANL)}$	Recessive output voltage at pin CANL	Standby mode; R _{LT} and C _{LT} not used	-0.1	0	0.1	V
$V_{o(off)(diff)}$	Differential bus output voltage (V _{CANH} – V _{CANL})	Standby mode; R _{LT} and C _{LT} not used	-0.2	0	0.2	V
$V_{o(dom)(CANH)}$	Dominant output voltage at pin CANH	$V_{TxD} = 0 \text{ V; } t < t_{dom(TxD);}$ $50 \Omega < R_{LT} < 65 \Omega$	2.75	3.5	4.5	V
$V_{o(dom)(CANL)}$	Dominant output voltage at pin CANL	$V_{TxD} = 0 \text{ V; } t < t_{dom(TxD);}$ $50 \Omega < R_{LT} < 65 \Omega$	0.5	1.5	2.25	V
$V_{o(dom)(diff)}$	Differential bus output voltage (V _{CANH} - V _{CANL})	V_{TxD} = 0 V; dominant; 45 Ω < R _{LT} < 65 Ω	1.5	2.25	3.0	V
V _{o(dom)(diff)_arb}	Differential bus output voltage during arbitration (V _{CANH} – V _{CANL})	$R_{LT} = 2.24 \text{ k}\Omega$ (Note 10)	1.5	-	5.0	٧
$V_{o(rec)(diff)}$	Differential bus output voltage (V _{CANH} - V _{CANL})	V _{TxD} = High; recessive; no load	-50	0	+50	mV
$V_{o(dom)(sym)}$	Dominant output voltage driver symmetry (VCANH + VCANL)	R_{LT} = 60 Ω ; C_1 = 4.7 nF; TxD = square wave up to 1 MHz	0.9	1.0	1.1	V _{CC}
I _{o(sc)(CANH)}	Short circuit output current at pin CANH	-3 V < V _{CANH} < +18 V	-100	-70	1.5	mA
I _{o(sc)(CANL)}	Short circuit output current at pin CANL	-3 V < V _{CANL} < +36 V	-1.5	70	100	mA
V _{i(rec)(diff)_NM}	Differential input voltage range recessive state	Normal or Silent mode; $-12 \text{ V} \leq \text{V}_{\text{CANH}}$, $\text{V}_{\text{CANL}} \leq +12 \text{ V}$; no load	-3.0	-	0.5	V
V _{i(rec)(diff)_LP}		Standby or Sleep mode; $-12 \text{ V} \leq \text{V}_{\text{CANH}}$, $\text{V}_{\text{CANL}} \leq +12 \text{ V}$; no load	-3.0		0.4	V
V _{i(dom)(diff)_NM}	Differential input voltage range dominant state	Normal or Silent mode; $-12 \text{ V} \leq \text{V}_{\text{CANH}}$, $\text{V}_{\text{CANL}} \leq +12 \text{ V}$; no load	0.9	_	8.0	V
$V_{i(dom)(diff)_LP}$		Standby or Sleep mode; -12 V ≤ V _{CANH} , V _{CANL} ≤ +12 V; no load	1.05		8.0	V
V _{i(diff)(th)_NORM}	Differential receiver threshold voltage in normal mode	-12 V ≤ V _{CANL} ≤ +12 V; -12 V ≤ V _{CANH} ≤ +12 V	0.5	-	0.9	V
$V_{i(diff)(th)_NORM_H}$	Differential receiver threshold voltage in normal mode, extended range	-30 V < V _{CANL} < +35 V; -30 V < V _{CANH} < +35 V	0.4	-	1.0	V
$V_{i(diff)(th)_STDBY}$	Differential receiver threshold voltage in standby mode	$-12 \text{ V} \le \text{V}_{CANL} \le +12 \text{ V};$ $-12 \text{ V} \le \text{V}_{CANH} \le +12 \text{ V}$	0.4	_	1.05	٧
R _{i(cm)(CANH)}	Common-mode input resistance at pin CANH	$-2 \text{ V} \le \text{V}_{CANH} \le +7 \text{ V};$ $-2 \text{ V} \le \text{V}_{CANL} \le +7 \text{ V}$	15	26	37	kΩ
R _{i(cm)(CANL)}	Common-mode input resistance at pin CANL	$-2 \text{ V} \le \text{V}_{CANH} \le +7 \text{ V};$ $-2 \text{ V} \le \text{V}_{CANL} \le +7 \text{ V}$	15	26	37	kΩ
R _{i(cm)(m)}	Matching between pin CANH and pin CANL common mode input resistance	V _{CANH} = V _{CANL} = +5 V	-1	0	+1	%
R _{i(diff)}	Differential input resistance	$-2 \text{ V} \le \text{V}_{CANH} \le +7 \text{ V};$ $-2 \text{ V} \le \text{V}_{CANL} \le +7 \text{ V}$	25	50	75	kΩ
C _{i(CANH)}	Input capacitance at pin CANH	V _{TxD} = High; (Note 10)	_	7.5	20	pF
C _{i(CANL)}	Input capacitance at pin CANL	V _{TxD} = High; (Note 10)	-	7.5	20	pF
C _{i(diff)}	Differential input capacitance	V _{TxD} = High; (Note 10)	_	3.75	10	pF

Table 5. ELECTRICAL CHARACTERISTICS V_{CC} = 4.75 V to 5.25 V; V_{IO} = 2.8 to 5.25 V; T_{J} = -40 to +150°C; R_{LT} = 60 Ω , C_{LT} = 100 pF, C_{LT} not used, C_{RxD} = 15 pF unless specified otherwise.

Symbol	Parameter	Min	Тур	Max	Unit	
TIMING CHARA	ACTERISTICS (see Figures 6 and 8)		•		•	
t _{d(TxD-BUSon)}	Delay TxD to bus active		-	75	-	ns
t _{d(TxD-BUSoff)}	Delay TxD to bus inactive		-	85	-	ns
t _{d(BUSon-RxD)}	Delay bus active to RxD		-	24	-	ns
t _{d(BUSoff-RxD)}	Delay bus inactive to RxD		-	32	-	ns
t _{pd_dr}	Propagation delay TxD to RxD dominant to recessive transition		50	100	210	ns
t _{pd_rd}	Propagation delay TxD to RxD recessive to dominant transition		50	120	210	ns
t _{d(stb-nm)}	Delay standby mode to normal mode		5	11	20	μs
t _{wake_filt}	Filter time for wake-up via bus	NCV7344 version	0.5	-	5	μs
		NCV7344A version	0.15	-	1.8	μs
t _{dwakerd}	Delay to flag wake event (recessive to dominant transitions)	Valid bus wake-up event	0.5	2.6	6	μs
t _{dwakedr}	Delay to flag wake event (dominant to recessive transitions)	Valid bus wake-up event	0.5	2.6	6	μs
t _{wake_to}	Bus time for wake-up timeout	Standby mode	1	-	10	ms
t _{dom(TxD)}	TxD dominant time for timeout	V _{TxD} = Low; Normal mode	1	_	10	ms
t _{Bit(RxD)}	Bit time on RxD pin	t _{Bit(TxD)} = 500 ns	400	_	550	ns
		t _{Bit(TxD)} = 200 ns	120	_	220	ns
t _{Bit(Vi(diff))}	Bit time on bus (CANH – CANL pin)	t _{Bit(TxD)} = 500 ns	435	_	530	ns
		t _{Bit(TxD)} = 200 ns	155	-	210	ns
Δt _{Rec} Receiver timing symmetry		$t_{Bit(TxD)} = 500 \text{ ns}$	-65	-	+40	ns
	$\Delta t_{Rec} = t_{Bit(RxD)} - t_{Bit(Vi(diff))}$	t _{Bit(TxD)} = 200 ns	-45	-	+15	ns
THERMAL SHU	ITDOWN		-	-	•	-
T _{J(sd)}	Shutdown junction temperature	Junction temperature rising	160	180	200	°C

^{9.} In the range between VUVD(VCC)(stby) and 4.75 V and from 5.25 V to 6 V the chip is fully functional; some parameters may be outside of the specification.

^{10.} Values based on design and characterization, not tested in production

MEASUREMENT SETUPS AND DEFINITIONS

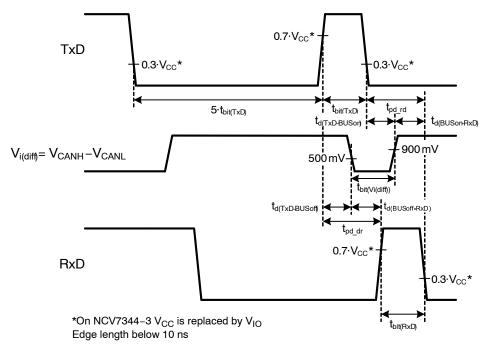


Figure 6. Transceiver Timing Diagram

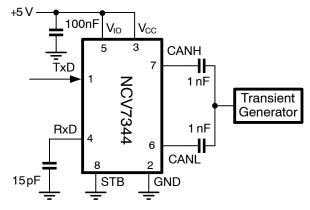


Figure 7. Test Circuit for Automotive Transients

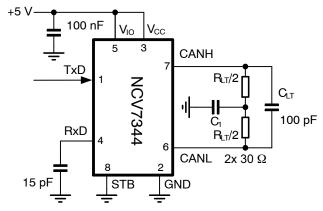


Figure 8. Test Circuit for Timing Characteristics

Table 6. ISO 11898-2:2016 Parameter Cross-Reference Table

ISO 11898–2:2016 Specification		NCV7344 Datasheet
Parameter	Notation	Symbol
Dominant output characteristics		
Single ended voltage on CAN_H	V _{CAN_H}	V _{o(dom)(CANH)}
Single ended voltage on CAN_L	V _{CAN_L}	V _{o(dom)(CANL)}
Differential voltage on normal bus load	V _{Diff}	$V_{o(dom)(diff)}$
Differential voltage on effective resistance during arbitration	V _{Diff}	V _{o(dom)(diff)_arb}
Differential voltage on extended bus load range (optional)	V_{Diff}	$V_{o(dom)(diff)}$
Driver symmetry	•	
Driver symmetry	V_{SYM}	$V_{o(dom)(sym)}$
Driver output current		
Absolute current on CAN_H	I _{CAN_H}	I _{o(SC)(CANH)}
Absolute current on CAN_L	I _{CAN_L}	I _{o(SC)(CANL)}
Receiver output characteristics, bus biasing active	<u> </u>	
Single ended output voltage on CAN_H	V _{CAN_H}	V _{o(rec)(CANH)}
Single ended output voltage on CAN_L	V _{CAN_L}	V _{o(rec)(CANL)}
Differential output voltage	V_{Diff}	V _{o(rec)(diff)}
Receiver output characteristics, bus biasing inactive	1	
Single ended output voltage on CAN_H	V _{CAN_H}	V _{o(off)(CANH)}
Single ended output voltage on CAN_L	V _{CAN_L}	V _{o(off)(CANL)}
Differential output voltage	V_{Diff}	$V_{o(off)(diff)}$
Optional transmit dominant timeout	<u> </u>	
Transmit dominant timeout, long	t _{dom}	t _{dom(TxD)}
Transmit dominant timeout, short	t _{dom}	NA
Static receiver input characteristics, bus biasing active	<u> </u>	
Recessive state differential input voltage range	V_{Diff}	V _{i(rec)(diff)_NM}
Dominant state differential input voltage range	V _{Diff}	V _{i(dom)(diff)_NM}
Static receiver input characteristics, bus biasing inactive	<u> </u>	
Recessive state differential input voltage range	V_{Diff}	V _{i(rec)(diff)_LP}
Dominant state differential input voltage range	V _{Diff}	V _{i(dom)(diff)} LP
Receiver input resistance	L	
Differential internal resistance	R _{Diff}	R _{i(diff)}
Single ended internal resistance	R _{CAN_H} R _{CAN_L}	R _{i(cm)(CANH)} R _{i(cm)(CANL)}
Receiver input resistance matching	•	
Matching a of internal resistance	m _R	R _{i(cm)(m)}
Implementation loop delay requirement	<u>I</u>	
Loop delay	t _{Loop}	t _{pd_rd} t _{pd_dr}
Optional implementation data signal timing requirements for use with bit rates	s above 1 Mbit/s and up to 2	
Transmitted recessive bit width @ 2 Mbit/s	t _{Bit(Bus)}	t _{Bit(Vi(diff))}
Received recessive bit width @ 2 Mbit/s	t _{Bit(RXD)}	t _{Bit(RxD)}

Table 6. ISO 11898-2:2016 Parameter Cross-Reference Table

Parameter	Notation	Symbol
Receiver timing symmetry @ 2 Mbit/s	Δt_{Rec}	Δ_{tRec}
Optional implementation data signal timing requirements for use with bit rates above	e 2 Mbit/s and up to 5 I	Mbit/s
Transmitted recessive bit width @ 5 Mbit/s	t _{Bit(Bus)}	t _{Bit(Vi(diff))}
Transmitted recessive bit width @ 5 Mbit/s	t _{Bit(RXD)}	t _{Bit(RxD)}
Received recessive bit width @ 5 Mbit/s	Δt_{Rec}	Δt_{Rec}
Maximum ratings of V _{CAN_H} , V _{CAN_L} and V _{Diff}		
Maximum rating V _{Diff}	V_{Diff}	V _{CANH-CANL}
General maximum rating V _{CAN_H} and V _{CAN_L}	V _{CAN_} H V _{CAN_} L	V _{CANH} V _{CANL}
Optional: Extended maximum rating V _{CAN_H} and V _{CAN_L}	V _{CAN_H} V _{CAN_L}	NA
Maximum leakage currents on CAN_H and CAN_L, unpowered		
Leakage current on CAN_H, CAN_L	I _{CAN_H} I _{CAN_L}	ILI
Bus biasing control timings		
CAN activity filter time, long	t _{Filter}	t _{wake_filt}
CAN activity filter time, short	t _{Filter}	t _{wake_filt}
Wake-up timeout, short	t _{Wake}	NA
Wake-up timeout, long	t _{Wake}	t _{wake_to}
Timeout for bus inactivity (Required for selective wake-up implementation only)	t _{Silence}	NA
Bus Bias reaction time (Required for selective wake-up implementation only)	t _{Bias}	NA

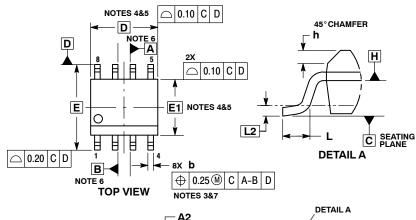
DEVICE ORDERING INFORMATION (High Speed Low Power CAN, CANFD Transceiver)

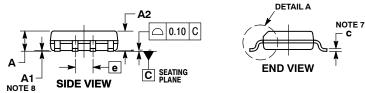
Part Number	Long FT	Short FT	Vio	NC	Temperature Range	Package	Shipping [†]	
NCV7344D10R2G	X			Х				
NCV7344D13R2G	Х		Х			SOIC 150 8 GREEN (Matte		
NCV7344AD10R2G		Х		Х		Sn, JEDEC MS-012) (Pb-Free)		
NCV7344AD13R2G		Х	Х				3000 / Tape &	
NCV7344MW0R2G	Х			Х	–40°C to +150°C		Reel	
NCV7344MW3R2G	Х		Х			DFN 8		
NCV7344AMW0R2G		Х		Х		Wettable Flank (Pb-Free)		
NCV7344AMW3R2G		Х	Х		1			

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

SOIC-8 CASE 751AZ **ISSUE B**





NOTES:

- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

 2. CONTROLLING DIMENSION: MILLIMETERS.

 3. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.004 mm IN EXCESS OF MAXIMUM MATERIAL CONDITION.
- MAXIMUM MATERIAL CONDITION.

 DIMENSION D DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS. SHALL NOT EXCEED 0.006 mm PER SIDE. DIMENSION E1 DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION. SHALL NOT EXCEED 0.010 mm PER SIDE. THE PACKAGE TOP MAY BE SMALLER THAN THE PACKAGE BOTTOM. DIMENSIONS D AND E1 ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AT DATUM H.

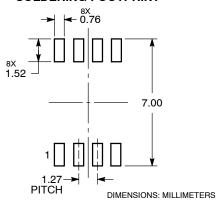
 DIMENSIONS A AND B ARE TO BE DETERMINED AT DATUM H.

 DIMENSIONS D AND C APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.10 TO 0.25 FROM THE LEAD TIP.

 A1 IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.

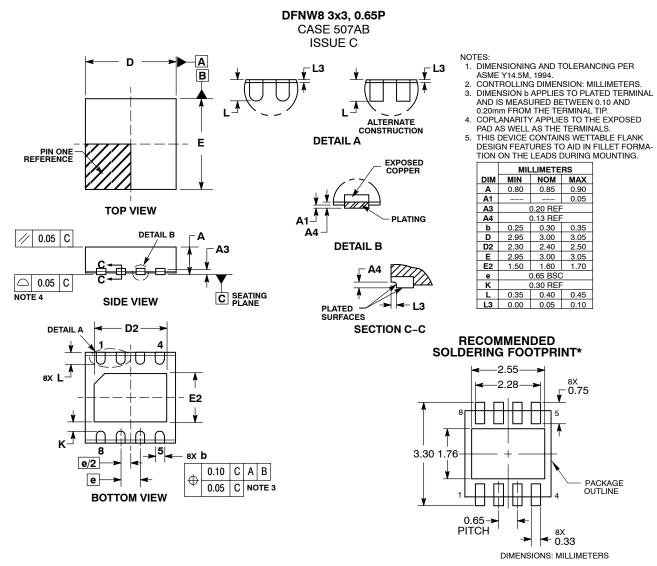
		IETEDO.					
	MILLIMETERS						
DIM	MIN	MAX					
Α	i	1.75					
A1	0.10	0.25					
A2	1.25						
b	0.31	0.51					
С	0.10	0.25					
D	4.90	BSC					
E	6.00	BSC					
E1	3.90	BSC					
е	1.27	BSC					
h	0.25	0.41					
L	0.40	1.27					
L2	0.25	BSC					

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and the are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. Coverage may be accessed at www.onsemi.com/site/par/-atent_-warking.pgr. On Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, earneges, and claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free

Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative